

### Abstract of the Disclosure

In a method of forming a film, the supply of a  
10 reaction gas is started at a first flow rate into a  
chamber in which a plasma is formed, such that an  
initial film is formed on a wafer. Then, the supply  
of the reaction gas is started at a second flow rate  
into the chamber in which the plasma is formed, such  
15 that the film is formed on the initial film, the first  
flow rate being smaller than the second flow rate.